



#### 60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
60V	$11m\Omega @ V_{GS} = 10V$	50A

### **Description**

This MOSFET is designed to minimize the on-state resistance  $(R_{DS(ON)})$ , yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- Power Management Functions
- DC-DC Converters
- Backlighting

#### **Features**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>G</sub> Minimizes Switching Losses
- <1.1mm Package Profile Ideal for Thin Applications</li>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (<u>DMNH6012SPSQ</u>)

#### **Mechanical Data**

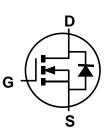
- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.097 grams (Approximate)



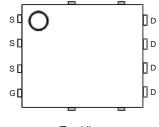
Top View



**Bottom View** 



Internal Schematic



Top View Pin Configuration

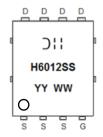
## **Ordering Information** (Note 4)

Part Number	Case	Packaging
DMNH6012SPS-13	PowerDI5060-8	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



☐ H=Manufacturer's Marking
H6012SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	60	V	
Gate-Source Voltage	$V_{GSS}$	±20	V	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	50 30	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	200	А	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	2.6	А	
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	I <sub>SM</sub>	200	А	
Avalanche Current, L = 0.1mH (Note 7)	I <sub>AS</sub>	45	А	
Avalanche Energy, L = 0.1mH (Note 7)	E <sub>AS</sub>	100	mJ	

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		$P_{D}$	1.6	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	93	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	51	
Total Power Dissipation (Note 6)		$P_D$	3.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	5	49	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	26	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	3.8		
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +175	°C	

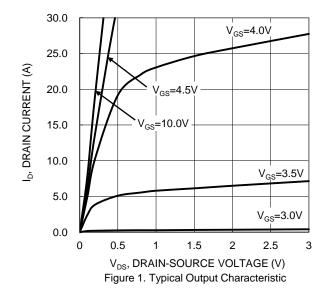
# **Electrical Characteristics** ( $@T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		60	_	_	V	$V_{GS} = 0V$ , $I_D = 250\mu A$	
Zero Gate Voltage Drain Current, T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_		1	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage		_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	2	_	4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	8	11	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.7A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>ISS</sub>	_	1,926	_	pF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz	
Output Capacitance	Coss	_	330	_	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	112	_	pF		
Gate Resistance	R <sub>G</sub>	_	2.0	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_G$	_	16.3	_	nC		
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_G$	_	35.2	_	nC	\/ 20\/ I- 25A	
Gate-Source Charge	$Q_{GS}$	_	7.6	_	nC	$V_{DS} = 30V, I_{D} = 25A$	
Gate-Drain Charge	$Q_{GD}$	_	6.9	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.4	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	11.9	_	ns	$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 3\Omega, I_D = 25A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	16.5	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	5	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	28	_	ns	I_ 25A di/dt 100A/vs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	23	_	$I_F = 25A$ , di/dt = 100A/ $\mu$ s		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
- 7. I $_{AS}$  and E $_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_{J}$  = +25°C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.





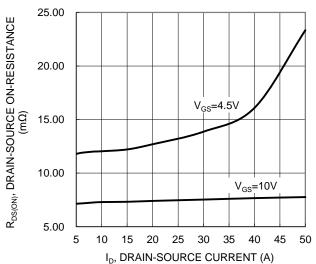


Figure 3. Typical On-Resistance vs. Drain Current and

Gate Voltage

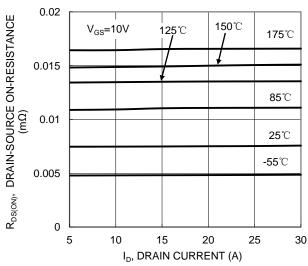
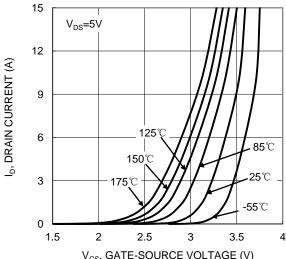
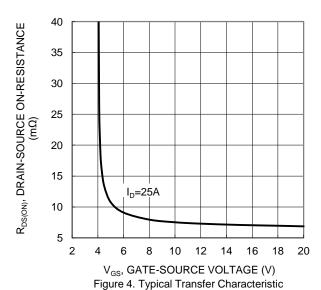


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



2.4  $R_{\mathrm{DS}(\mathrm{ON})}$ , DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2.2 2  $V_{GS} = 10V, I_{D} = 25A$ 1.8 1.6 1.4 1.2  $V_{GS}$ =4.5V,  $I_{D}$ =25A 1 8.0 0.6 0.4 -25 0 25 50 75 100 125 150 175 -50



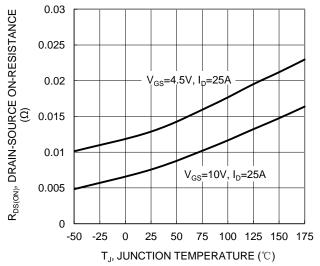
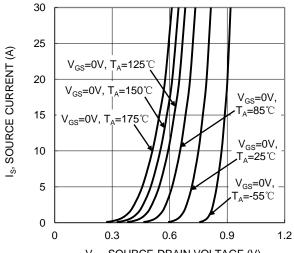


Figure 7. On-Resistance Variation with Temperature



 $V_{SD}$ , SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

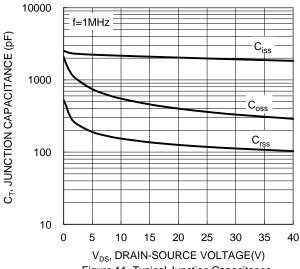


Figure 11. Typical Junction Capacitance

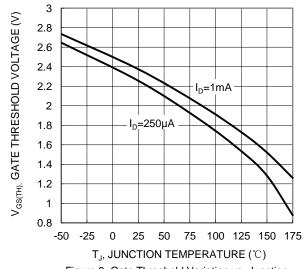
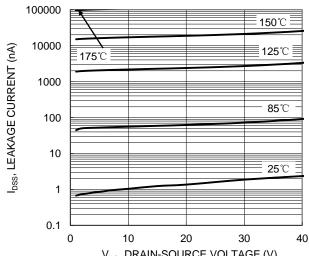


Figure 8. Gate Threshold Variation vs. Junction Temperature



 $V_{DS}$ , DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Drain-Source Leakage Current vs. Voltage

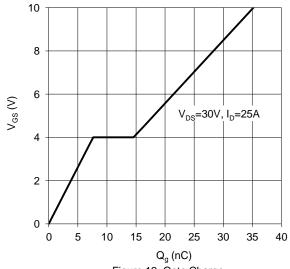
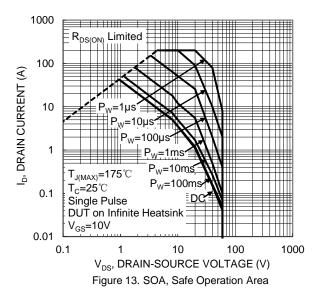
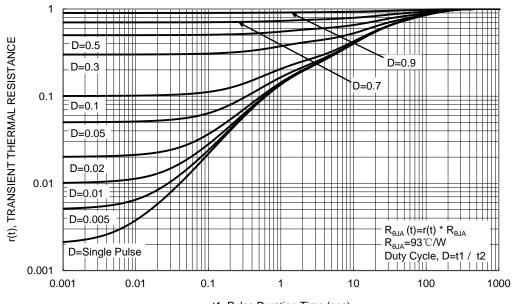


Figure 12. Gate Charge







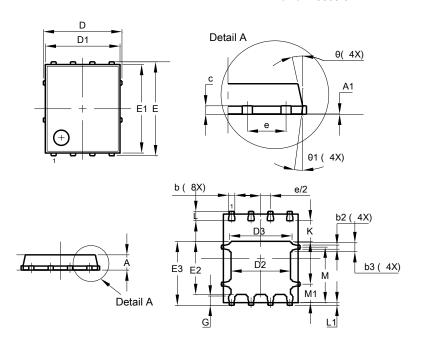
t1, Pulse Duration Time (sec)
Figure 14. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

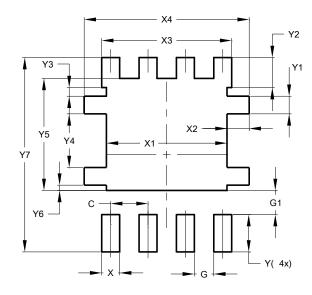


PowerDI5060-8					
Dim	Min	Тур			
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90 4.30 4.10				
E	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
Х3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610



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